

MAXIMUM RATINGS

Rating	Symbol	MM5415	MM5416	Unit
Collector-Emitter Voltage	V _{CEO}	200	300	Vdc
Collector-Base Voltage	V _{CBO}	200	350	Vdc
Emitter-Base Voltage	V _{EBO}	4.0	7.0	Vdc
Base Current	I _B	0.5		Adc
Collector Current — Continuous	I _C	1.0		.Adc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	1.0	6.7	Watt W/°C
Total Power Dissipation @ T _C = 50°C Linear Derating Factor	P _D	10	0.057	Watts mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	R _{θJC}	17.5	°C/W
Thermal Resistance, Junction to Ambient	R _{θJA}	150	°C/W

MM5415 MM5416

CASE 79-02, STYLE 1
TO-39 (TO-205AD)

TRANSISTOR

PNP SILICON

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Refer to 2N5415 for graphs.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Sustaining Voltage (I _C = 10 mA, I _B = 0)	V _{CEO(sus)}	200 300	—	Vdc
Collector Cutoff Current (V _{CE} = 150 Vdc, I _B = 0)	I _{CEO}	—	50	μAdc
Collector Cutoff Current (V _{CE} = 175 Vdc, I _E = 0) (V _{CE} = 280 Vdc, I _E = 0)	I _{CBO}	— —	50 50	μAdc μAdc
Emitter Cutoff Current (V _{BE} = 4.0 Vdc, I _C = 0) (V _{BE} = 7.0 Vdc, I _C = 0)	I _{EBO}	— —	20 20	μAdc

ON CHARACTERISTICS

DC Current Gain (I _C = 50 mAdc, V _{CE} = 10 Vdc)	h _{FE}	30 30	150 120	—
Collector-Emitter Saturation Voltage (I _C = 50 mAdc, I _B = 5.0 mAdc)	V _{CE(sat)}	—	2.5	Vdc
Base-Emitter On Voltage (I _C = 50 mAdc, V _{CE} = 10 V)	V _{BE(on)}	—	1.5	Vdc

SMALL-SIGNAL CHARACTERISTICS

Current-Gain — Bandwidth Product (I _C = 10 mAdc, V _{CE} = 10 Vdc, f = 5.0 MHz)	f _T	15	—	MHz
Output Capacitance (V _{CB} = 10 Vdc, f = 1.0 MHz)	C _{obo}	—	25	pF
Current Gain — High Frequency (I _C = 5.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)	h _{fe}	25	—	—
Real Part of Input Impedance (I _C = 5.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 MHz)	Re(h _{ie})	—	300	Ohms